

Switch-mode Power Rectifier

60 V, 20 A

MBR20L60CTG MBRF20L60CTG

Features and Benefits

- Low Power Loss/High Efficiency
- High Surge Capacity
- 20 A Total (10 A Per Diode Leg)
- Guard-Ring for Stress Protection
- These Devices are Pb-Free and are RoHS Compliant*

Applications

- Power Supply Output Rectification
- Power Management
- Instrumentation

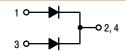
Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped 50 Units Per Plastic Tube

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

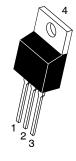
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SCHOTTKY BARRIER RECTIFIER 20 AMPERES 60 VOLTS

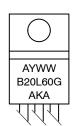


TO-220 CASE 221A

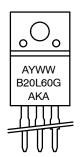
STYLE 6



MARKING DIAGRAM







A = Assembly Location Y = Year WW = Work Week B20L60 = Device Code

G = Pb-Free Package AKA = Polarity Designator

ORDERING INFORMATION

Device	Package	Shipping
MBR20L60CTG	TO-220 (Pb-Free)	50 Units / Rail
MBRF20L60CTG	TO-220FP (Pb-Free)	50 Units / Rail

MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	60	V
Average Rectified Forward Current MBR20L60CT (Rated V_R) T_C = 138°C Per Diode MBRF20L60CT (Rated V_R) T_C = 123°C Per Device	I _{F(AV)}	10 20	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	240	А
Operating Junction Temperature (Note 1)	TJ	-55 to +150	°C
Storage Temperature	T _{stg}	- 65 to +175	°C
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V
Maximum Repetitive Peak Avalanche Voltage $(t_p < 1~\mu s, T_J < 150^{\circ}C, I_{AR} < 51~A)$	V _{ARM}	85	V
Maximum Single-Pulse Peak Avalanche Voltage ($t_p < 1~\mu s, T_J < 150^{\circ} C, I_{AR} < 51~A$)	V _{ASM}	85	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

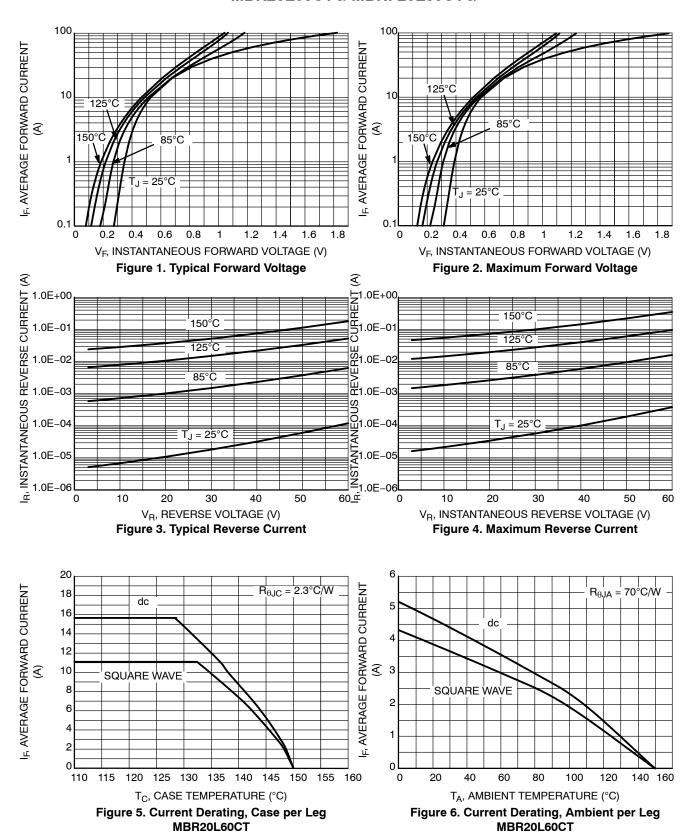
Charac	Symbol	Value	Unit	
Maximum Thermal Resistance				°C/W
MBR20L60CTG	Junction-to-Case	$R_{\theta JC}$	2.3	
	Junction-to-Ambient	$R_{\theta JA}$	70	
MBRF20L60CTG	Junction-to-Case	$R_{ heta JC}$	5.2	
	Junction-to-Ambient	$R_{\theta JA}$	75	

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Тур	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 10 \text{ A}$, $T_C = 25^{\circ}\text{C}$) ($I_F = 10 \text{ A}$, $T_C = 125^{\circ}\text{C}$) ($I_F = 20 \text{ A}$, $T_C = 25^{\circ}\text{C}$) ($I_F = 20 \text{ A}$, $T_C = 125^{\circ}\text{C}$)	VF	0.53 0.49 0.68 0.64	0.57 0.54 0.73 0.69	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 25^{\circ}C$) (Rated DC Voltage, $T_C = 125^{\circ}C$)	İR	118 52	380 96	μ A mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{2.} Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤[2.0%.



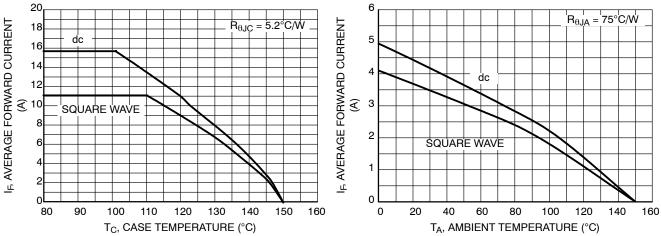


Figure 7. Current Derating, Case per Leg MBRF20L60CT

Figure 8. Current Derating, Ambient per Leg MBRF20L60CT

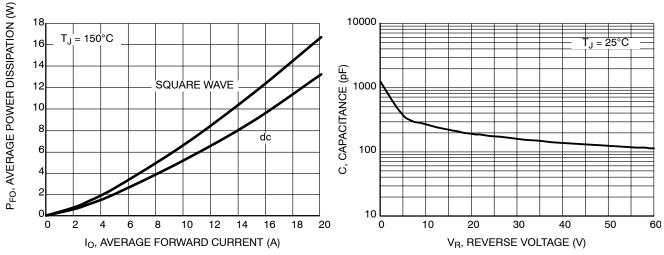


Figure 9. Forward Power Dissipation

Figure 10. Capacitance

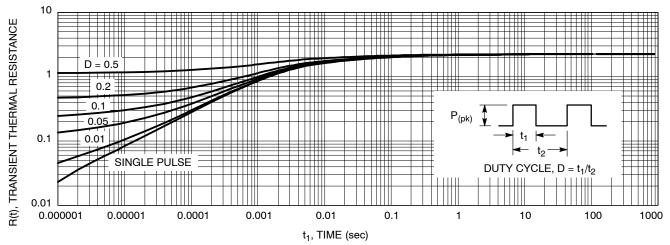


Figure 11. Thermal Response Junction-to-Case, per Leg for MBR20L60CT

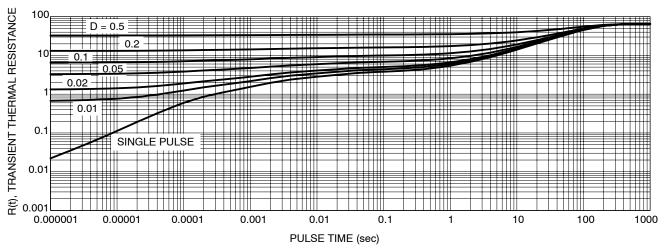


Figure 12. Thermal Response Junction-to-Ambient, per Leg for MBR20L60CT

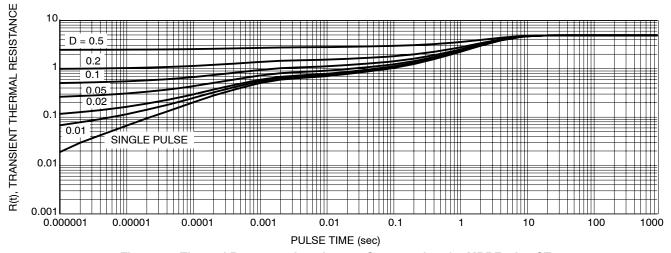


Figure 13. Thermal Response Junction-to-Case, per Leg for MBRF20L60CT

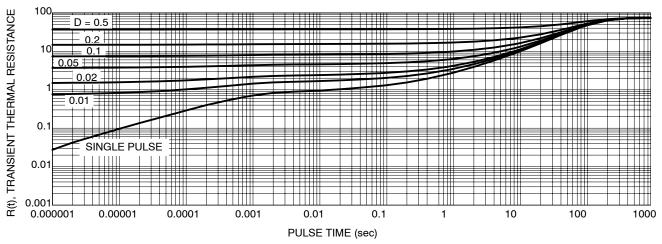


Figure 14. Thermal Response Junction-to-Ambient, per Leg for MBRF20L60CT

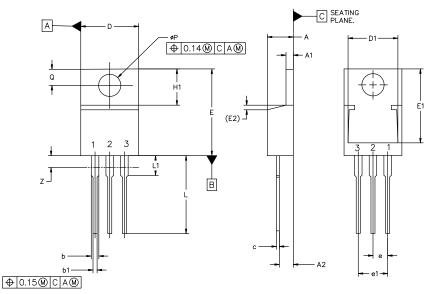
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TO-220-3 10.10x15.12x4.45, 2.54P CASE 221A **ISSUE AL**

DATE 05 FEB 2025



MILLIMETERS				
DIM	MIN	NOM	MAX	
Α	4.07	4.45	4.83	
A1	1.15	1.28	1.41	
A2	2.04	2.42	2.79	
b	1.15	1.34	1.52	
b1	0.64	0.80	0.96	
С	0.36	0.49	0.61	
D	9.66	10.10	10.53	
D1	8.43	8.63	8.83	
Е	14.48	15.12	15.75	
E1	12.58	12.78	12.98	
E2	1.27 REF			

MILLIMETERS				
DIM	MIN	NOM	MAX	
е	2.42	2.54	2.66	
e1	4.83	5.08	5.33	
H1	5.97	6.22	6.47	
L	12.70	13.49	14.27	
L1	2.80	3.45	4.10	
Q	2.54	2.79	3.04	
ØΡ	3.60	3.85	4.09	
Z	-,	-,	3.48	

NOTES:

- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.

 2. CONTROLLING DIMENSION: MILLIMETERS.

 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

STYLE 1:		STYLE 2:		STYLE 3:		STYLE 4:	
PIN 1.	BASE	PIN 1.	BASE	PIN 1.	CATHODE	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	EMITTER	2.	ANODE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	COLLECTOR	3.	GATE	3.	GATE
4.	COLLECTOR	4.	EMITTER	4.	ANODE	4.	MAIN TERMINAL 2
STYLE 5:		STYLE 6:		STYLE 7:		STYLE 8:	
PIN 1.	GATE	PIN 1.	ANODE	PIN 1.	CATHODE	PIN 1.	CATHODE
2.	DRAIN	2.	CATHODE	2.	ANODE	2.	ANODE
3.	SOURCE	3.	ANODE	3.	CATHODE	3.	EXTERNAL TRIP/DELAY
4.	DRAIN	4.	CATHODE	4.	ANODE	4.	ANODE
STYLE 9:		STYLE 10:		STYLE 11:	:	STYLE 12:	:
PIN 1.	GATE	PIN 1.	GATE	PIN 1.	DRAIN	PIN 1.	MAIN TERMINAL 1
2.	COLLECTOR	2.	SOURCE	2.	SOURCE	2.	MAIN TERMINAL 2
3.	EMITTER	3.	DRAIN	3.	GATE	3.	GATE
4.	COLLECTOR	4.	SOURCE	4.	SOURCE	4.	NOT CONNECTED

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SCALE 1:1

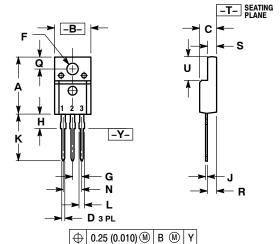
TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH
- 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.617	0.635	15.67	16.12
В	0.392	0.419	9.96	10.63
С	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100	BSC	2.54 BSC	
Н	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200	BSC	5.08	BSC
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

MARKING DIAGRAMS



CATHODE
 ANODE

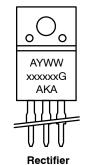
STYLE 1: PIN 1. GATE STYLE 2: PIN 1. BASE STYLE 3: PIN 1. ANODE 2. COLLECTOR 3. EMITTER 2. DRAIN 2. 3. SOURCE STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE STYLE 4: PIN 1. CATHODE

STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE ANODE 3. CATHODE

O xxxxxxG **AYWW**

Bipolar xxxxxx = Specific Device Code G = Pb-Free Package

Α = Assembly Location Υ = Year = Work Week WW



= Assembly Location

= Polarity Designator

Υ = Year = Work Week WW XXXXXX = Device Code = Pb-Free Package G

AKA

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